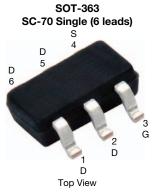
SQ1440EH



Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	60					
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.120					
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.150					
I _D (A)	1.7					
Configuration	Single					
Package	SC-70					

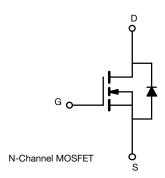


FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



Marking Code: 9G

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \degree C$, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	60	V		
Gate-Source Voltage		V _{GS}	± 20	V		
Continuous Drain Current ^a	T _C = 25 °C	I_	1.7			
Continuous Drain Current ~	T _C = 125 °C	ID	1.7			
Continuous Source Current (Diode Conduction	on) ^a	I _S	1.7	А		
Pulsed Drain Current ^b		I _{DM}	6.7			
Single Pulse Avalanche Current		I _{AS}	10			
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	5	mJ		
Maximum Dawar Dissinction b	T _C = 25 °C	D	3.3	W		
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	1.1	vv		
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL	LIMIT	UNIT			
Junction-to-Ambient	PCB Mount ^c		125	°C/W			
Junction-to-Foot (Drain)		R _{thJF}	45	0/10			

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static				<u> </u>	1		1
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 60 V, T _J = 175 °C	-	-	150	1 .
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	Α
		$V_{GS} = 10 V$	I _D = 3.8 A	-	0.085	0.120	Ω
Drain Course On State Desistance 8	Р	V _{GS} = 10 V	I _D = 3.8 A, T _J = 125 °C	-	-	0.200	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	I _D = 3.8 A, T _J = 175 °C	-	-	0.240	
		$V_{GS} = 4.5 V$	I _D = 3.1 A	-	0.095	0.150	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 1.8 A		-	6	-	S
Dynamic ^b	•	•		•	•		
Input Capacitance	C _{iss}		V _{DS} = 15 V, f = 1 MHz	-	275	344	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	34	42	
Reverse Transfer Capacitance	C _{rss}			-	13	17	
Total Gate Charge ^c	Qg			-	4.4	5.5	nC
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 3.8 \text{ A}$	-	0.7	-	
Gate-Drain Charge ^c	Q _{gd}			-	1.3	-	
Gate Resistance	Rg	f = 1 MHz		2.1	4.1	6.2	Ω
Turn-On Delay Time ^c	t _{d(on)}				5.8	7.3	- ns
Rise Time ^c	tr	$\begin{array}{l} V_{DD}=30~V,~R_{L}=3.9~\Omega\\ I_{D}\cong3.8~A,~V_{GEN}=10~V,~R_{g}=1~\Omega \end{array}$		-	23	29	
Turn-Off Delay Time ^c	t _{d(off)}			-	10	13	
Fall Time ^c	t _f			-	30	39	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	11	Α
Forward Voltage	V _{SD}	I _F =	_	0.8	1.2	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

0.25

15

0.20 $R_{DS(on)}$ - On-Resistance (Ω) 0.15 $V_{GS} = 4.5 V$ 0.10 V_{GS} = 10 V 0.05 0.00 0 3 6 9 12 15 I_D - Drain Current (A)

On-Resistance vs. Drain Current

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8

10

150 175

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

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= 10 V thru 4 V 12 12 I_D - Drain Current (A) I_D - Drain Current (A) 9 9 V_{GS}= 3 V $T_{C} = 25 \ ^{\circ}C$ 6 6 3 3 125 $V_{GS} = 1 V$ T_C = - 55 °C $V_{GS} = 2 V$ 0 0 0 2 3 4 5 0 2 1 4 6 V_{DS} - Drain-to-Source Voltage (V) V_{GS} - Gate-to-Source Voltage (V) **Output Characteristics Transfer Characteristics** 80 15 I_D = 10 mA V_{DS} - Drain-to-Source Voltage (V) 76 12 g_{fs} - Transconductance (S) T_C = - 55 °C 9 72 T_C = 25 °C 6 68 T_C = 125 °C 3 64 0 60 2 3 4 0 1 5 - 50 - 25 25 75 100 125 0 50 I_D - Drain Current (A) T_{.1} - Junction Temperature (°C) Transconductance Drain Source Breakdown vs. Junction Temperature 500 400 C - Capacitance (pF) Ciss 300 200 100 $\mathsf{C}_{\mathrm{oss}}$ 0 0 15 30 45 60 V_{DS} - Drain-to-Source Voltage (V)

Capacitance

3

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S15-2675-Rev. B, 16-Nov-15

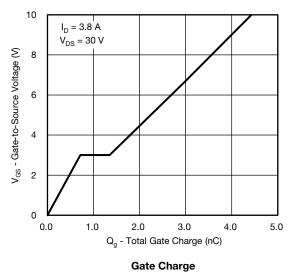
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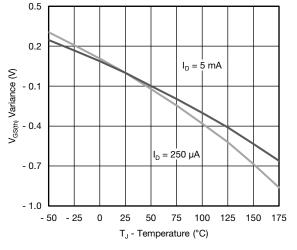
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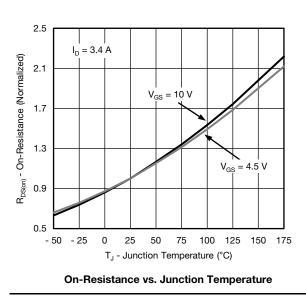
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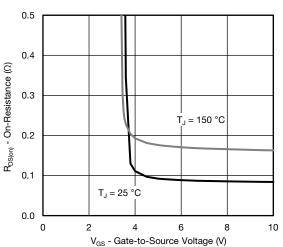
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



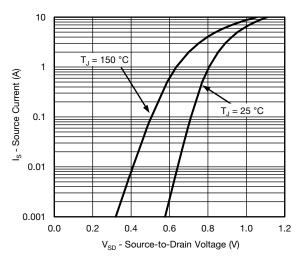




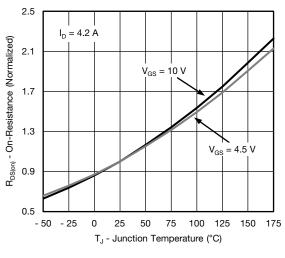




On-Resistance vs. Gate-to-Source Voltage







On-Resistance vs. Junction Temperature

S15-2675-Rev. B, 16-Nov-15

4

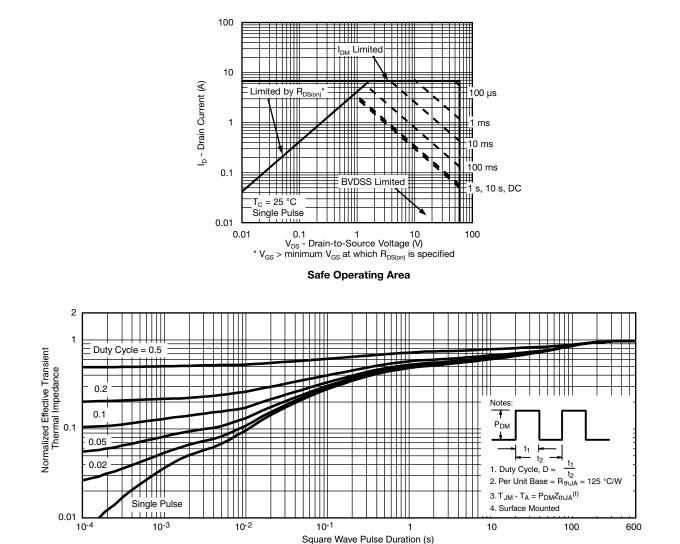
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



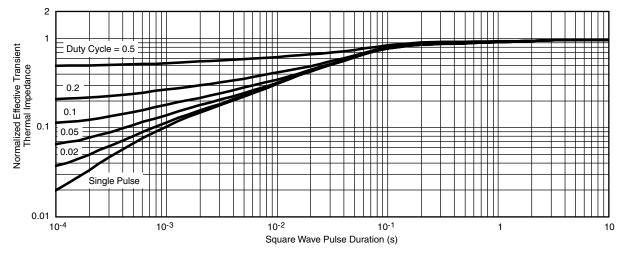
Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65884.

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SQ1440EH

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REVISION HISTORY^a

REVISION	DATE	DESCRIPTION OF CHANGE
В	05-Nov-15	Corrected marking code

Note

a. As of April 2014



Package Information Vishay Siliconix

SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
С	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
٩	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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